

Features

- High isolation 5000 VRMS
- CTR flexibility available see order information
- DC input with transistor output
- Operating temperature range 55 ℃ to 110 ℃
- Regulatory Approvals
 - UL UL1577 (E364000)
 - VDE EN60747-5-5(VDE0884-5)
 - CQC GB4943.1, GB8898
 - IEC60065, IEC60950

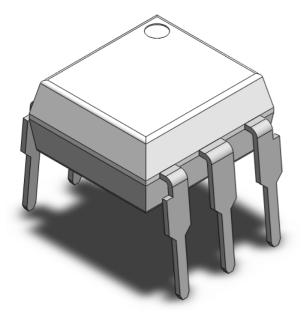
Applications

- Switch mode power supplies
- Computer peripheral interface
- Microprocessor system interface

Description

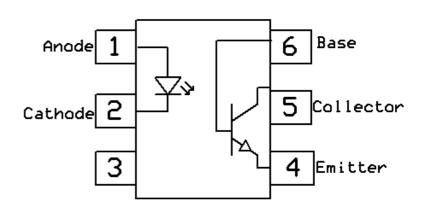
The 4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5 series consists of a photo transistor optically coupled to a gallium arsenide Infrared-emitting diode in a 6-lead DIP package different lead forming options.

Package Outline



Note: Different bending options available. See package dimension.

Schematic





Absolute Maximum Rating at 25°C

Symbol	Parameters	Ratings	Units	Notes
Viso	Isolation voltage	5000	V _{RMS}	
Topr	Operating temperature	-55 ~ +110	°C	
Тѕтс	Storage temperature	-55 ~ +150	°C	
Tsol	Soldering temperature	260	°C	
Emitter		•		
l _F	Forward current	60	mA	
I _{F(TRANS)}	Peak transient current (≤1µs P.W,300pps)	1	А	
VR	Reverse voltage	6	V	
P _D	Power dissipation	100	mW	
Detector		•		
P _D	Power dissipation	150	mW	
B _{VCEO}	Collector-Emitter Breakdown Voltage	80	V	
Вусво	Collector-Base Breakdown Voltage	80	V	
Bveco	Emitter-Collector Breakdown Voltage	7	V	
B _{VEBO}	Emitter-Base Breakdown Voltage	7	V	



Electrical Characteristics $T_A = 25 \, ^{\circ}\text{C}$ (unless otherwise specified)

Emitter Characteristics

Symbol	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
VF	Forward voltage	I _F =10mA		1.24	1.4	٧	
IR	Reverse Current	V _R = 6V	-	-	5	μΑ	
C _{IN}	Input Capacitance	f= 1MHz	-	45	-	pF	

Detector Characteristics

Symbol	Pa	rameters	Test Conditions	Min	Тур	Max	Units	Notes
Bvceo	Collector-Emitter I	Breakdown	Ic= 0.1mA	80	-	-	٧	
Bveco	Emitter-Collector I	Breakdown	I _E = 0.1mA	7	-	-	٧	
Вусво	Collector-Base Bro	eakdown	Ic= 0.1mA	80	-	-	٧	
B _{VEBO}	Emitter-Base Brea	akdown	I _E = 0.1mA	7	-	-	٧	
Iceo	Collector-Emitter Dark Current	4N25,4N26,4N27,4N28 H11A1,A2,A3,A4,A5	V _{CE} = 10V, I _F =0mA	-	-	50	nA	
		4N35,4N36,4N37,4N38	V _{CE} =60V, I _F =0mA	-	-	50	nA	
Ісво	Collector-Base Da	ark Current	V _{CB} = 10V, I _F =0mA	-	-	20	nA	

Transfer Characteristics

Symbol	Parameters		Test Conditions	Min	Тур	Max	Units	Notes	
		4N35		100	-	-			
		4N25,4N26, 4N38,		00					
		H11A2, H11A3	I _F = 10mA, V _{CE} = 10V		20	-	-		
OTD	Current	4N27, 4N28, H11A4		10	-	-	%		
CTR	Transfer	H11A1		50	-	-			
	Ratio	H11A5		30	-	-			
		4N36	L 0 A W 5W	130	-	260			
		4N37	I _F = 2mA, V _{CE} = 5V	200	-	400			
	Collector-E	4N25,4N26, 4N27,4N28	I _F = 50mA, I _C = 2mA	-	-	0.5			
	mitter	4N35,4N36,4N37	I _F = 10mA, I _C = 0.5mA	-	-	0.3			
V _{CE} (SAT)	Saturation Voltage	H11A1,H11A2, H11A3,H11A4,H11A5		-	-	0.4	V		
		4N38	I _F = 20mA, I _C = 4mA	-	-	1.0			



Transfer Characteristics

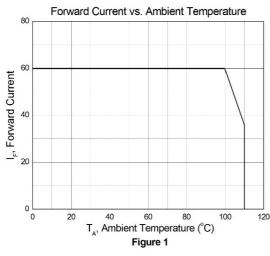
R _{IO}	Isolation Resistance	$V_{IO} = 500 V_{DC}$	1x10 ¹¹		Ω	
Сю	Isolation Capacitance	f= 1MHz		0.25	рF	

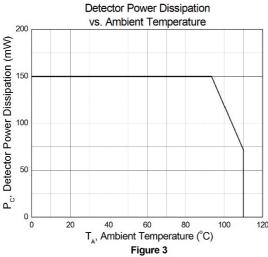
Switching Characteristics

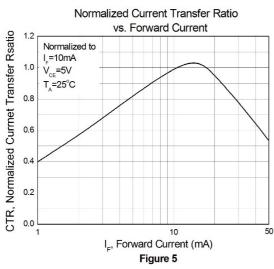
Symbol	F	Parameters	Test Conditions	Min	Тур	Max	Units	Notes
		4N25,4N26,4N27,4N28	I _F = 10mA, V _{CC} = 10V, R _L =		- 4.3			
+	Turn On	H11A1,A2,A3,A4,A5	100Ω	,	4.0	9.8		
ton	Time	4N35,4N36,4N37,4N38	I_{c} = 2mA, V_{CC} = 10V, R_{L} =	- 9.8	0.0 11.6	11.5	μs	
		41133,41136,41137,41136	100Ω		11.3			
		4N25,4N26,4N27,4N28	I _F = 10mA, V _{CC} = 10V, R _L =		3.9	9.8		
+	Turn Off	H11A1,A2,A3,A4,A5	100Ω	-	3.9	9.0		
t _{off}	Time	4N25 4N26 4N27 4N29	I _c = 2mA, V _{CC} = 10V, R _L =	- 6.9	0.0	44.5	μs	
		4N35,4N36,4N37,4N38	100Ω		11.5			

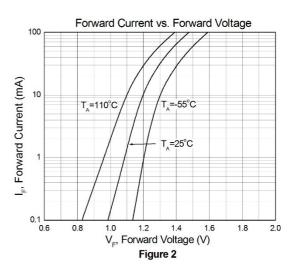


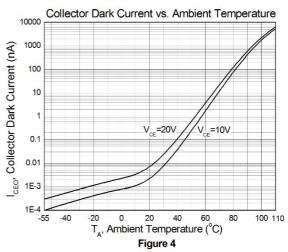
Typical Characteristic Curves

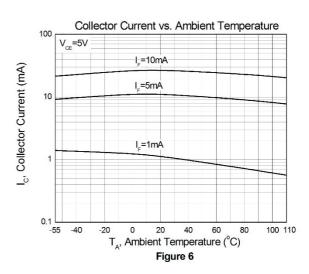




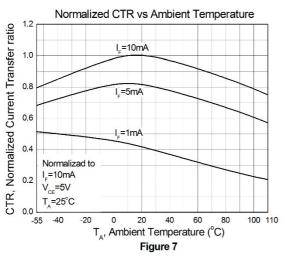


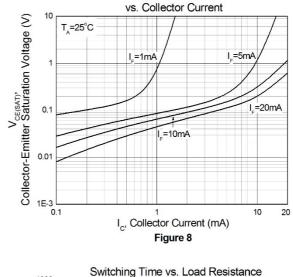




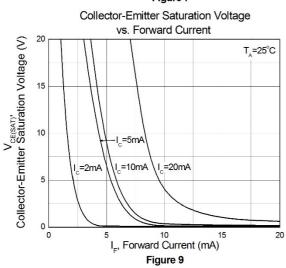


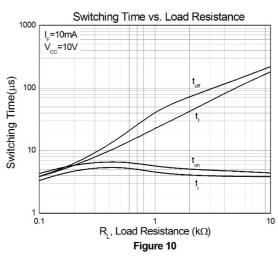


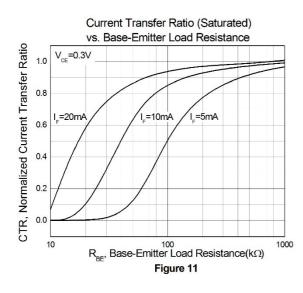


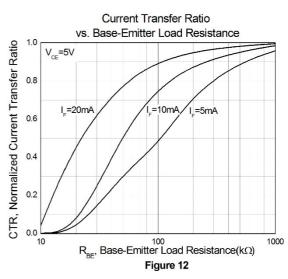


Collector-Emitter Stauration Voltage

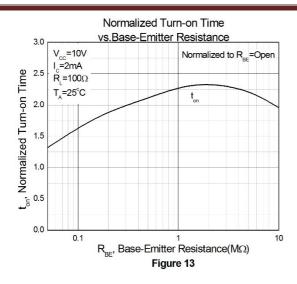


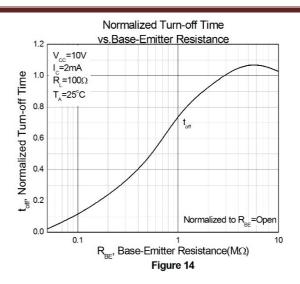








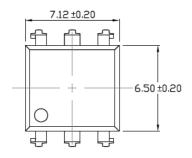


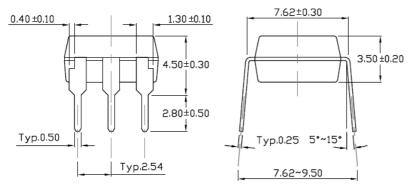




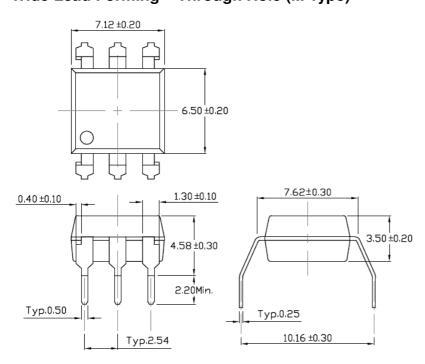
Package Dimension Dimensions in mm unless otherwise stated

Standard DIP - Through Hole



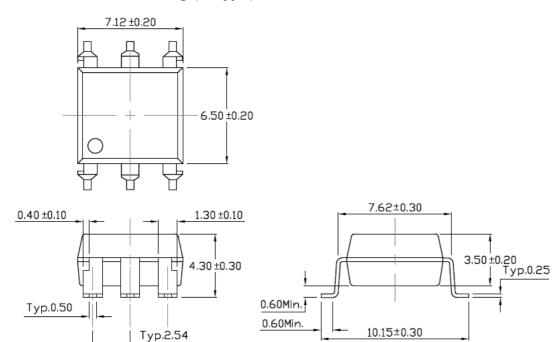


Wide Lead Forming – Through Hole (M Type)

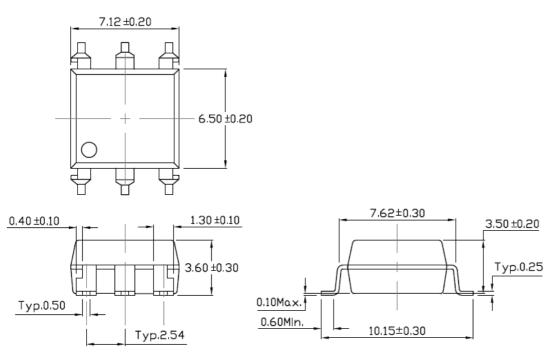




Surface Mount Forming (S Type)

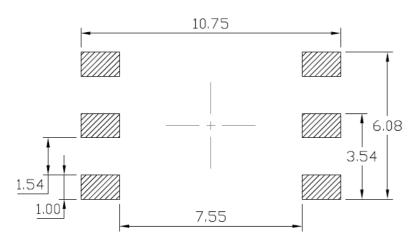


Surface Mount Forming (Low Profile) (SL Type)

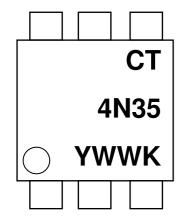




Recommended Solder Mask Dimensions in mm unless otherwise stated



Marking Information



Note:

CT : Denotes "CT Micro"

4N35 : Part Number
Y : Fiscal Year
WW : Work Week

K : Manufacturing Code



Ordering Information

4N2X(Y)(Z)-G, 4N3X(Y)(Z)-G, H11AX(Y)(Z)-G

X = Part No.

(4N25, 4N26, 4N27, 4N28, 4N35, 4N36, 4N37, 4N38, H11A1, H11A2, H11A3, H11A4, H11A5)

Y = Lead form option (S, SL, M or none)

Z = Tape and reel option (T1, T2 or none)

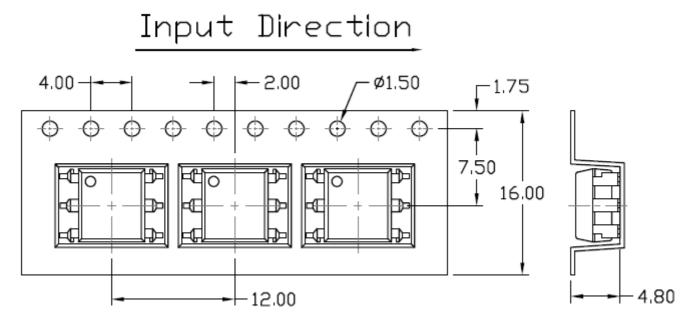
G= Material option (G: Green, None: Non-green)

Option	Description	Quantity
None	Standard 6 Pin Dip	50Units/Tube
М	Wide Lead Forming	50Units/Tube
S(T1)	Surface Mount Lead Forming – With Option A Taping	1000 Units/Reel
S(T2)	Surface Mount Lead Forming – With Option B Taping	1000 Units/Reel
SL(T1)	Surface Mount Lead Forming(Low Profile) – With Option A Taping	1000 Units/Reel
SL(T2)	Surface Mount Lead Forming(Low Profile) – With Option B Taping	1000 Units/Reel



Carrier Tape Specifications Dimensions in mm unless otherwise stated

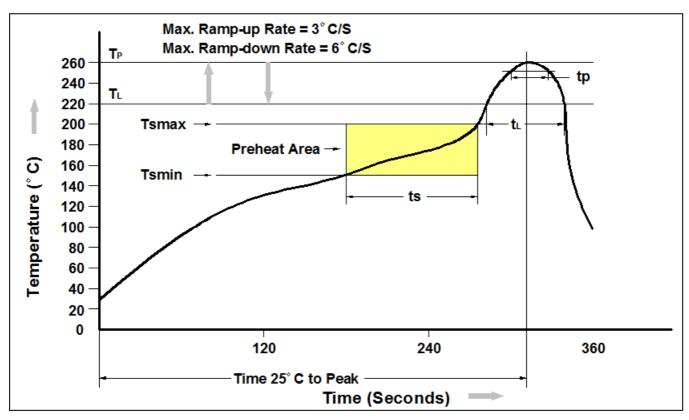
Option S(T1) & SL(T1)



Option S(T2) & SL(T2)



Reflow Profile



Profile Feature	Pb-Free Assembly Profile
Temperature Min. (Tsmin)	150℃
Temperature Max. (Tsmax)	200℃
Time (ts) from (Tsmin to Tsmax)	60-120 seconds
Ramp-up Rate (t _L to t _P)	3 ℃/second max.
Liquidous Temperature (TL)	217℃
Time (t _L) Maintained Above (T _L)	60 - 150 seconds
Peak Body Package Temperature	260℃ +0℃ / -5℃
Time (t _P) within 5 °C of 260 °C	30 seconds
Ramp-down Rate (T _P to T _L)	6°C/second max
Time 25 ℃ to Peak Temperature	8 minutes max.



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